## INK0010AC1-T150

#### High Speed Switching Silicon N-channel MOSFET

AEC-Q101 COMPLIANCE

#### DESCRIPTION

INK0010AC1 is a Silicon N-channel MOSFET.

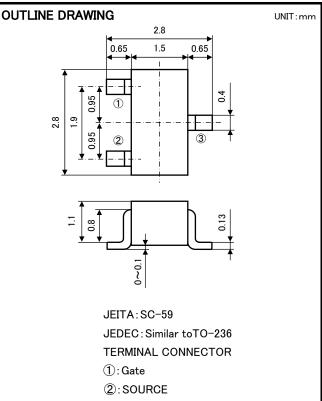
This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

### FEATURE

- •Input impedance is high, and not necessary to consider a drive electric current.
- •Drive voltage 4V
- -Low on Resistance. RDS(ON)=4.0  $\Omega$  (TYP) @ID=100mA, VGS=4.0V
- $RDS(ON)=3.0 \Omega(TYP) @ID=100mA, VGS=10V$
- ·High speed switching.
- •Small package for easy mounting.

### APPLICATION

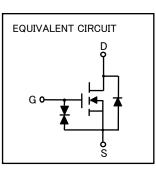
High speed switching , Analog switching

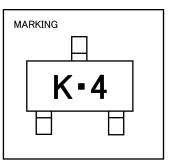


3: DRAIN

| •                            |   |   |
|------------------------------|---|---|
| PARAMETER                    | RATING  | UNIT  |
| Drain-source voltage         | 60  | V   |
| Gate-source voltage          | ±20   | V   |
| Drain current(DC)            | 260   | mA  |
| Drain current(Pulse) ※1      | 800   | mA  |
| Total power dissipation      | 200   | mW  |
| Channel temperature          | +150  | °C  |
| Range of Storage temperature | -55 <b>~</b> +150   | °C  |
|                              | Drain-source voltage<br>Gate-source voltage<br>Drain current(DC)<br>Drain current(Pulse) ※1<br>Total power dissipation<br>Channel temperature | Drain-source voltage60Gate-source voltage±20Drain current(DC)260Drain current(Pulse) ※1800Total power dissipation200Channel temperature+150 |

### MAXIMUM RATING (Ta= $25^{\circ}$ C)





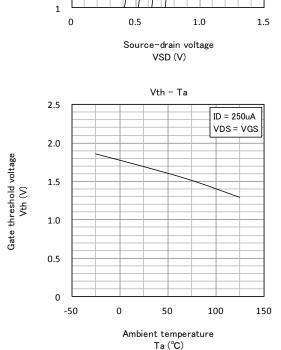
%1: Pw $\leq 10 \,\mu$  s, Duty cycle $\leq 1\%$ 

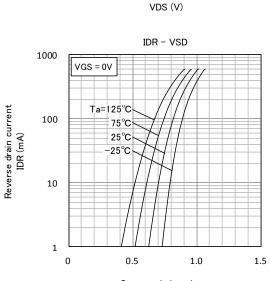
### ELECTRICAL CHARACTERISTICS (Ta=25°C)

| PARAMETER                               | SYMBOL   | TEST CONDITION  | LIMIT |     |      | UNIT |
|---|----------|---|-------|-----|------|------|
|   |          |   | MIN   | TYP | MAX  | UNIT |
| Drain-source breakdown voltage          | V(BR)DSS | $I_{\rm D}$ =100 $\mu$ A, V <sub>GS</sub> =0V               | 60    | -   | -    | V    |
| Gate-source leak current                | Igss     | $V_{GS} = \pm 15V, V_{DS} = 0V$                             | -     | -   | ±1.0 | μA   |
| Zero gate voltage drain current         | Idss     | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                   | -     | -   | 1.0  | μA   |
| Gate threshold voltage                  | Vth      | $I_{\rm D}$ =250 $\mu$ A, V <sub>DS</sub> = V <sub>GS</sub> | 1.0   | -   | 2.0  | V    |
| Forward transfer admittance             | Yfs      | V <sub>DS</sub> =10V, I <sub>D</sub> =100mA                 | -     | 200 | -    | mS   |
| Static drain-source on-state resistance | RDS(ON)  | I <sub>D</sub> =100mA, V <sub>GS</sub> =4.0V                | -     | 4.0 | _    | Ω    |
|   |          | I <sub>D</sub> =100mA, V <sub>GS</sub> =10V                 | -     | 3.0 | -    |      |
| Input capacitance                       | Ciss     | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz           | -     | 20  | -    | pF   |
| Output capacitance                      | Coss     |   | -     | 5.0 | -    | pF   |
| Switching time                          | ton      | V <sub>DD</sub> =5V, I <sub>D</sub> =10mA                   | -     | 27  | -    | ns   |
|   | toff     | V <sub>GS</sub> =0~5V                                       | -     | 58  | -    | ns   |

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**TYPICAL CHARACTERISTICS** 

500

400

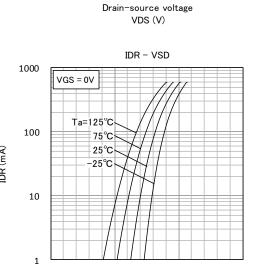
300

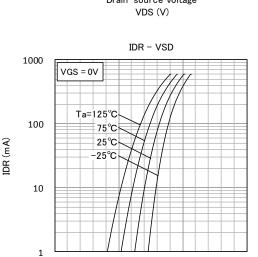
200

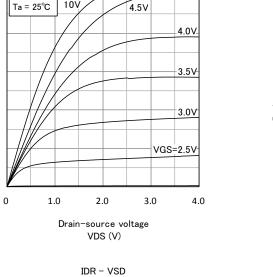
100

0

Drain current ID (mA)

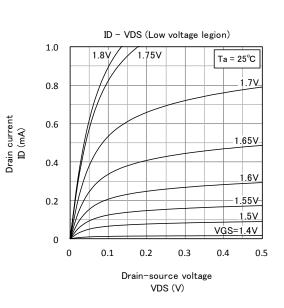


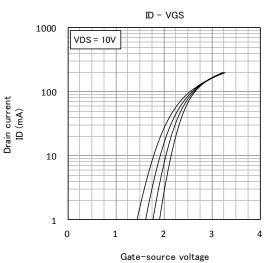




ID - VDS

10V





VGS (V)

|Yfs| - ID

1000

100

10

1

1

Forward transfer admittance |Yfs| (mS)

VDS = 10V

Ta=125°C

75°C

25°C

25°C

10

100

Drain current

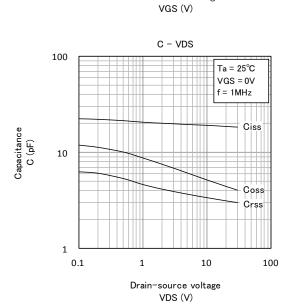
ID (mA)

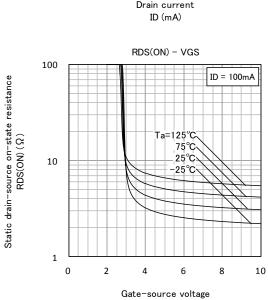
1000

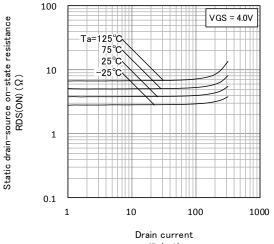
INK0010AC1-T150

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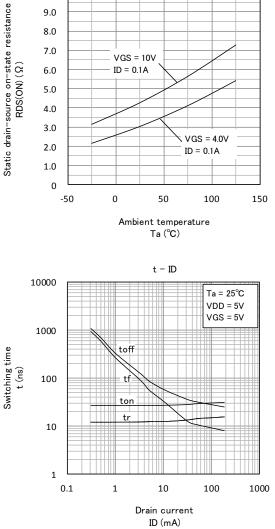
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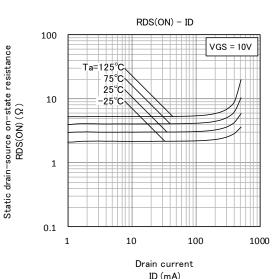


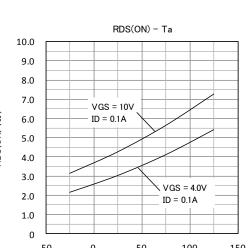


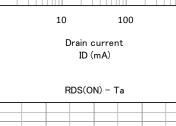


RDS(ON) - ID



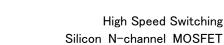






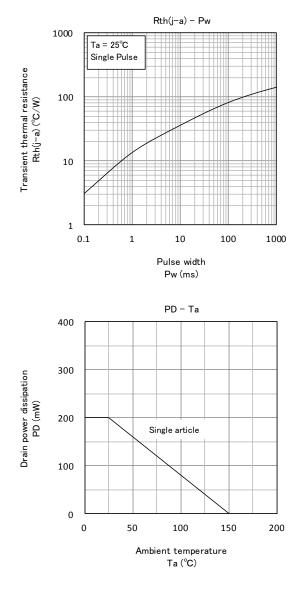


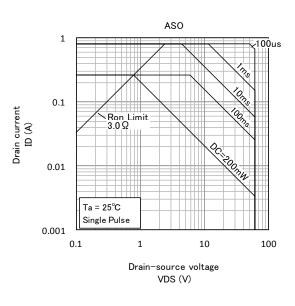
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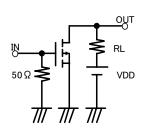
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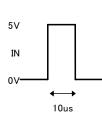
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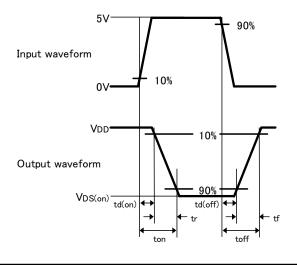


Switching time test condition





 $\begin{array}{l} \text{Duty} \leq 1\% \\ \text{Input:tr, tf} < 10 \text{ns} \\ \text{VDD} = 5 \text{V} \\ \text{Common source} \\ \text{Ta} = 25^\circ \text{C} \end{array}$ 



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